查询2N7016供应商

Siliconix incorporated

2N7016 T-39-17

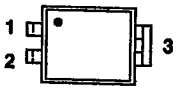
P-Channel Enhancement Mode Transistor

PRODUCT SUMMARY

$V_{(BR)DSS}$ (V)	$r_{DS(ON)}$ (Ω)	I_D (A)
−60	1.0	−0.70

4-PIN DIP
(Similar to TO-250)

TOP VIEW



1 GATE
2 SOURCE
3 DRAIN

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C Unless Otherwise Noted)[1]

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current	T_A = 25°C	I_D	0.70	A
	T_A = 100°C		0.45	
Pulsed Drain Current[2]		I_{DM}	10	
Power Dissipation	T_A = 25°C	P_D	1.0	W
	T_A = 100°C		0.4	
Operating Junction & Storage Temperature Range		T_J, T_{stg}	−55 to 150	°C
Lead Temperature ($1/16$" from case for 10 sec.)		T_L	300	

4

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient	R_{thJA}		120	K/W

[1]Negative signs for current and voltage ratings have been omitted for the sake of clarity.
[2]Pulse width limited by maximum junction temperature.

This Material Copyrighted By Its Respective Manufacturer

2N7016

Siliconix incorporated

ELECTRICAL CHARACTERISTICS (T_J = 25°C Unless Otherwise Noted)
P-Channel Device – Negative Signs Have Been Omitted for Clarity

PARAMETER	SYMBOL	TEST CONDITIONS	TYP	LIMITS MIN	LIMITS MAX	UNIT
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 µA		60		V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 1000 µA		2.0	4.0	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = $V_{(BR)DSS}$, V_{GS} = 0 V			250	µA
		V_{DS} = 0.8 x $V_{(BR)DSS}$, V_{GS} = 0 V, T_J = 125°C			1000	
On-State Drain Current[1]	$I_{D(ON)}$	V_{DS} = 5 V, V_{GS} = 10 V		0.7		A
Drain-Source On-State Resistance[1]	$r_{DS(ON)}$	V_{GS} = 10 V, I_D = 0.70 A	0.85		1.0	Ω
		V_{GS} = 10 V, I_D = 0.70 A, T_J = 125°C	1.6		1.9	
Forward Transconductance[1]	g_{fs}	V_{DS} = 15 V, I_D = 2 A	0.90	0.50		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz	200		290	pF
Output Capacitance	C_{oss}		110		160	
Reverse Transfer Capacitance	C_{rss}		25		60	
Total Gate Charge[2]	Q_g	V_{DS} = 0.8 x $V_{(BR)DSS}$, V_{GS} = 10 V, I_D = 0.7 A	6.1		7.5	nC
Gate-Source Charge[2]	Q_{gs}		0.8			
Gate-Drain Charge[2]	Q_{gd}		3.5			
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DD} = 40 V, R_L = 40 Ω, I_D ≅ 1 A, V_{GEN} = 10 V, R_G = 25 Ω	8		20	ns
Rise Time[2]	t_r		9		20	
Turn-Off Delay Time[2]	$t_{d(off)}$		16		25	
Fall Time[2]	t_f		25		30	
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_A = 25°C)						
Continuous Current	I_S				0.70	A
Pulsed Current[3]	I_{SM}				10	
Forward Voltage[1]	V_{SD}	I_F = I_S, V_{GS} = 0 V	1.3		1.8	V
Reverse Recovery Time	t_{rr}	I_F = I_S, dI_F/dt = 100 A/µs	60			ns
Reverse Recovery Charge	Q_{rr}		0.15			µC

[1]Pulse test: Pulse Width ≤ 300 µsec, Duty Cycle ≤ 2%.
[2]Independent of operating temperature.
[3]Pulse width limited by maximum junction temperature).

This Material Copyrighted By Its Respective Manufacturer

Siliconix incorporated

2N7016

TYPICAL CHARACTERISTICS (25°C Unless Otherwise Specified)

Figure 1. Output Characteristics

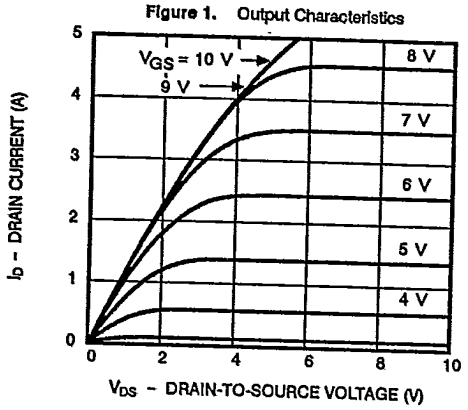


Figure 2. Transfer Characteristics

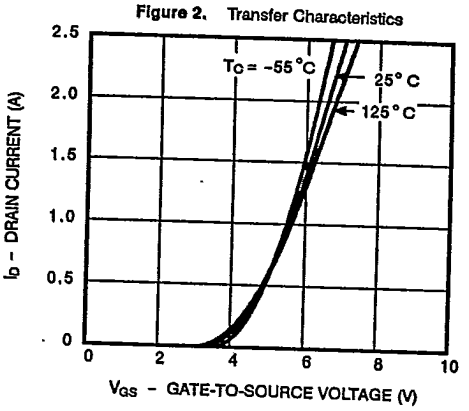


Figure 3. Transconductance

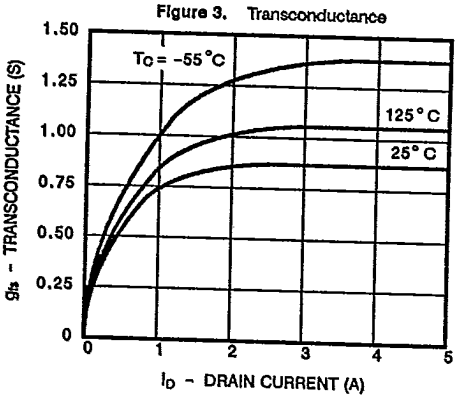


Figure 4. On-Resistance

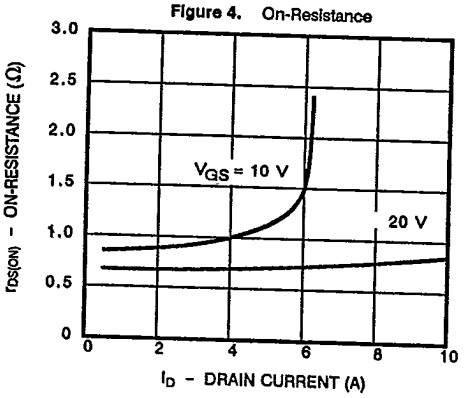


Figure 5. Capacitance

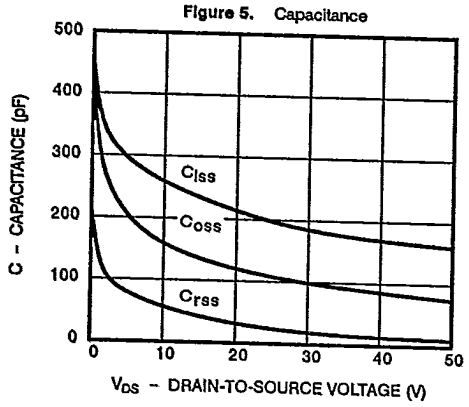
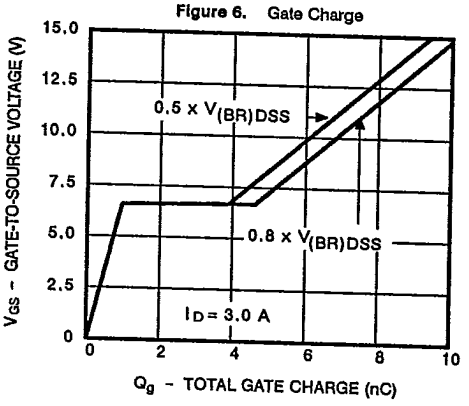


Figure 6. Gate Charge



4

This Material Copyrighted By Its Respective Manufacturer

2N7016

Siliconix incorporated

TYPICAL CHARACTERISTICS (Cont'd)

Figure 7. On-Resistance vs. Junction Temperature

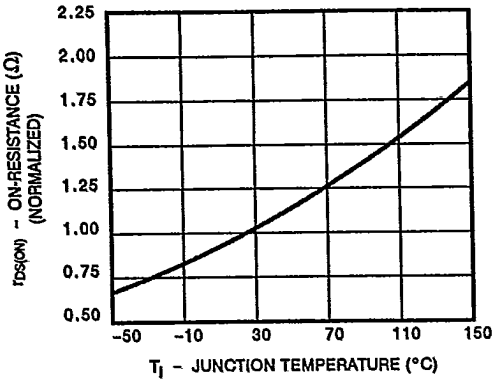
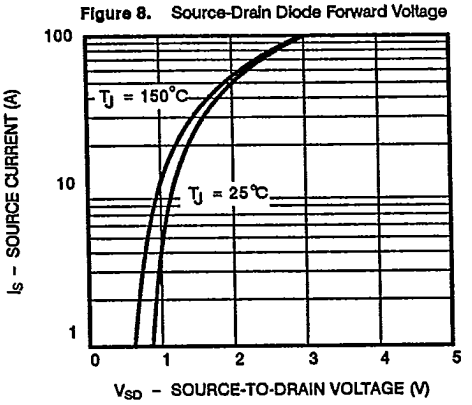


Figure 8. Source-Drain Diode Forward Voltage



THERMAL RATINGS

Figure 9. Maximum Drain Current vs. Ambient Temperature

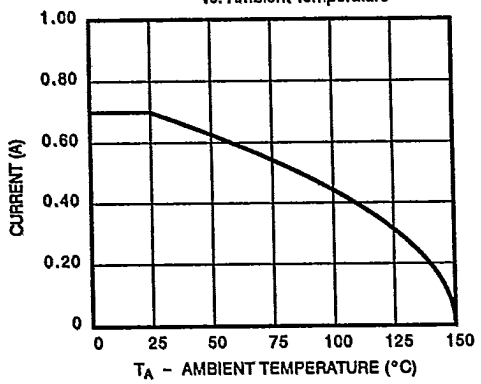
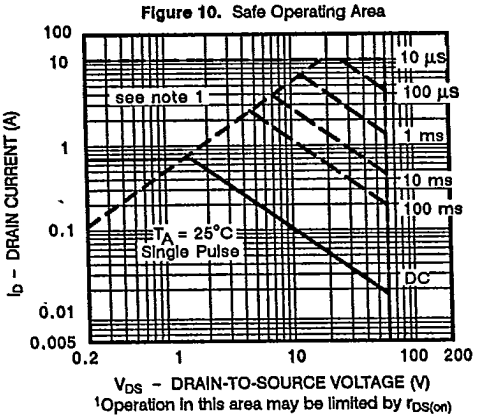


Figure 10. Safe Operating Area



[1]Operation in this area may be limited by $r_{DS(on)}$

This Material Copyrighted By Its Respective Manufacturer